

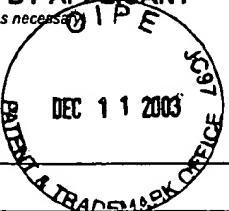
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PTO/SB/05A (0-01)

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		Complete if Known	
		Application Number	09/256643
		Filing Date	February 23, 1999
		First Named Inventor	Forbes, Leonard
		Group Art Unit	2822
		Examiner Name	Trinh, Michael
		Sheet 1 of 2	
Attorney Docket No: 303.324US2			

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Michael Trinh

DATE CONSIDERED

1/22/04

Substitute Disclosure Statement Form (PTO-1448)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT P E <i>(Use as many sheets as necessary)</i>		Complete if Known	
		Application Number	09/256643
		Filing Date	February 23, 1999
		First Named Inventor	Forbes, Leonard
		Group Art Unit	2822
		Examiner Name	Trinh, Michael
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